

2 A, 1.2 V, Slew Rate Controlled Load Switch

DESCRIPTION

The SiP32411 is a slew rate controlled load switch that is designed for 1.1 V to 5.5 V operation.

The device guarantees low switch on-resistance at 1.2 V input. It features a controlled soft-on slew rate of typical 150 μ s that limits the inrush current for designs of capacitive load or noise sensitive loads.

The device features a low voltage control logic interface (On/Off interface) that can interface with low voltage digital control without extra level shifting circuit. It also integrates an output discharge switch that enables fast shutdown load discharge. When the switch is off, it provides the reverse blocking to prevent high current flowing into the power source.

The SiP32411DN is in TDFN4 package of 1.2 mm by 1.6 mm. It supports over 2 A of continuous current. The SiP32411DR is in SC70-6 package.

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- 1.1 V to 5.5 V operation voltage range
- 62 m Ω typical from 2 V to 5 V for SiP32411DN
- 101 m Ω typical from 2 V to 5 V for SiP32411DR
- Low R_{ON} down to 1.2 V
- Slew rate controlled turn-on: 150 μ s at 3.6 V
- Fast shutdown load discharge
- Low quiescent current
 - < 1 μ A when disabled
 - 6.7 μ A at $V_{IN} = 1.2$ V
- Switch off reversed blocking
- **Compliant to RoHS Directive 2002/95/EC**



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Cellular phones
- Portable media players
- Digital camera
- GPS
- Computers
- Portable instruments and healthcare devices

TYPICAL APPLICATION CIRCUIT

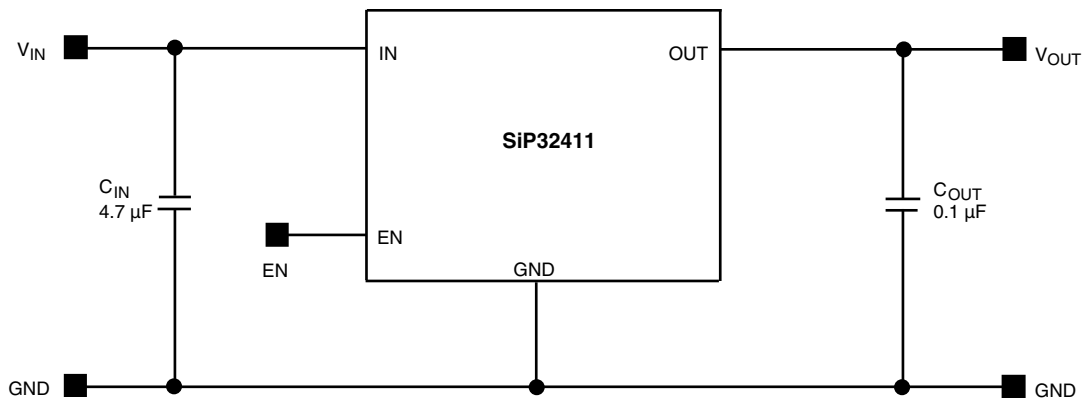


Figure 1 - SiP32411 Typical Application Circuit

ORDERING INFORMATION

Temperature Range	Package	Marking	Part Number
- 40 °C °C to 85 °C	SC70-6	MBxx	SiP32411DR-T1-GE3
	TDFN4 1.2 mm x 1.6 mm	AEx	SiP32411DNP-T1-GE4

Notes:

x = Lot code

GE3 and GE4 denote halogen-free and RoHS compliant

ABSOLUTE MAXIMUM RATINGS

Parameter		Limit	Unit
Supply Input Voltage (V_{IN})		- 0.3 to 6	V
Enable Input Voltage (V_{EN})		- 0.3 to 6	
Output Voltage (V_{OUT})		- 0.3 to $V_{IN} + 0.3$	
Maximum Continuous Switch Current ($I_{max.}$)	SC70-6 package	1.8	A
	TDFN4 1.2 mm x 1.6 mm	2.4	
Maximum Pulsed Current (I_{DM}) V_{IN} (Pulsed at 1 ms, 10 % Duty Cycle)	SC70-6 package	2.2	
	TDFN4 1.2 mm x 1.6 mm	3	
ESD Rating (HBM)		4000	V
Junction Temperature (T_J)		- 40 to 125	°C
Thermal Resistance (θ_{JA}) ^a	6 pin SC70-6 ^b	240	°C/W
	4 pin TDFN4 1.2 mm x 1.6 mm ^c	170	
Power Dissipation (P_D) ^a	6 pin SC70-6 ^b	230	mW
	4 pin TDFN4 1.2 mm x 1.6 mm ^c	324	

Notes:

a. Device mounted with all leads and power pad soldered or welded to PC board, see PCB layout.

b. Derate 4.5 mW/°C above $T_A = 70$ °C, see PCB layout.c. Derate 5.9 mW/°C above $T_A = 70$ °C, see PCB layout.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE

Parameter	Limit	Unit
Input Voltage Range (V_{IN})	1.1 to 5.5	V
Operating Temperature Range	- 40 to 85	°C

SPECIFICATIONS

Parameter	Symbol	Test Conditions Unless Specified V _{IN} = 5 V, T _A = - 40 °C to 85 °C (Typical values are at T _A = 25 °C)		Limits - 40 °C to 85 °C			Unit
				Min. ^a	Typ. ^b	Max. ^a	
Operating Voltage ^c	V _{IN}			1.1	-	5.5	V
Quiescent Current	I _Q	V _{IN} = 1.2 V, EN = active		-	6.7	14	μA
		V _{IN} = 1.8 V, EN = active		-	14	24	
		V _{IN} = 2.5 V, EN = active		-	25	40	
		V _{IN} = 3.6 V, EN = active		-	40	60	
		V _{IN} = 4.3 V, EN = active		-	52	75	
		V _{IN} = 5 V, EN = active		-	71	99	
Off Supply Current	I _{Q(off)}	EN = inactive, OUT = open		-	-	1	
Off Switch Current	I _{DS(off)}	EN = inactive, OUT = GND		-	-	1	
Reverse Blocking Current	I _{RB}	V _{OUT} = 5 V, V _{IN} = 1.2 V,V _{EN} = inactive		-	-	10	
On-Resistance	R _{DS(on)}	SC70-6	V _{IN} = 1.2 V, I _L = 100 mA, T _A = 25 °C	-	105	125	mΩ
			V _{IN} = 1.8 V, I _L = 100 mA, T _A = 25 °C	-	101	120	
			V _{IN} = 2.5 V, I _L = 100 mA, T _A = 25 °C	-	101	120	
			V _{IN} = 3.6 V, I _L = 100 mA, T _A = 25 °C	-	101	120	
			V _{IN} = 4.3 V, I _L = 100 mA, T _A = 25 °C	-	101	120	
			V _{IN} = 5 V, I _L = 100 mA, T _A = 25 °C	-	101	120	
		TDFN4 1.2 mm x 1.6 mm	V _{IN} = 1.2 V, I _L = 100 mA, T _A = 25 °C	-	66	76	
			V _{IN} = 1.8 V, I _L = 100 mA, T _A = 25 °C	-	62	72	
			V _{IN} = 2.5 V, I _L = 100 mA, T _A = 25 °C	-	62	72	
			V _{IN} = 3.6 V, I _L = 100 mA, T _A = 25 °C	-	62	72	
			V _{IN} = 4.3 V, I _L = 100 mA, T _A = 25 °C	-	62	72	
			V _{IN} = 5 V, I _L = 100 mA, T _A = 25 °C	-	62	72	
On-Resistance Temp.-Coefficient	TC _{RDS}	SC70-6 package		-	4300	-	ppm/°C
		TDFN4 1.2 mm x 1.6 mm package		-	3400	-	
EN Input Low Voltage ^c	V _{IL}	V _{IN} = 1.2 V		-	-	0.3	V
		V _{IN} = 1.8 V		-	-	0.4 ^d	
		V _{IN} = 2.5 V		-	-	0.5 ^d	
		V _{IN} = 3.6 V		-	-	0.6 ^d	
		V _{IN} = 4.3 V		-	-	0.7 ^d	
		V _{IN} = 5 V		-	-	0.8 ^d	
EN Input High Voltage ^c	V _{IH}	V _{IN} = 1.2 V		0.9 ^d	-	-	
		V _{IN} = 1.8 V		1.2 ^d	-	-	
		V _{IN} = 2.5 V		1.4 ^d	-	-	
		V _{IN} = 3.6 V		1.6 ^d	-	-	
		V _{IN} = 4.3 V		1.7 ^d	-	-	
		V _{IN} = 5 V		1.8	-	-	
EN Input Leakage	I _{SINK}	V _{EN} = 5.5 V		- 1	-	1	μA
Output Pulldown Resistance	R _{PD}	EN = inactive, T _A = 25 °C		-	217	280	Ω
Output Turn-On Delay Time	t _{d(on)}	V _{IN} = 3.6 V, R _{LOAD} = 10 Ω, T _A = 25 °C		-	140	210	μs
Output Turn-On Rise Time	t _(on)			80	150	220	
Output Turn-Off Delay Time	t _{d(off)}			-	0.27	1	

Notes:

a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum.

b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

c. For V_{IN} outside this range consult typical EN threshold curve.

d. Not tested, guarantee by design.

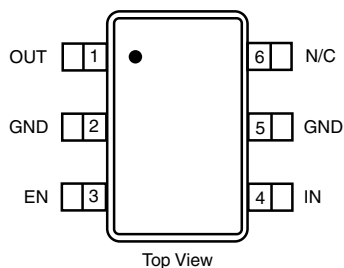
PIN CONFIGURATION

Figure 2 - SC70-6 Package

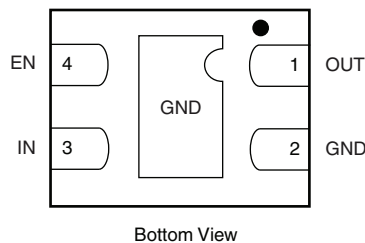


Figure 3 - TDFN4 1.2 mm x 1.6 mm Package

PIN DESCRIPTION

Pin Number		Name	Function
SC70-6	TDFN4		
4	3	IN	This pin is the n-channel MOSFET drain connection. Bypass to ground through a 2.2 μ F capacitor.
2, 5	2	GND	Ground connection
3	4	EN	Enable input
1	1	OUT	This pin is the n-channel MOSFET source connection. Bypass to ground through a 0.1 μ F capacitor.

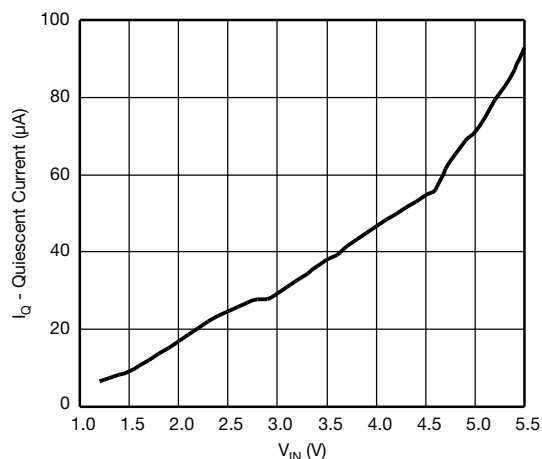
TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

Figure 4 - Quiescent Current vs. Input Voltage

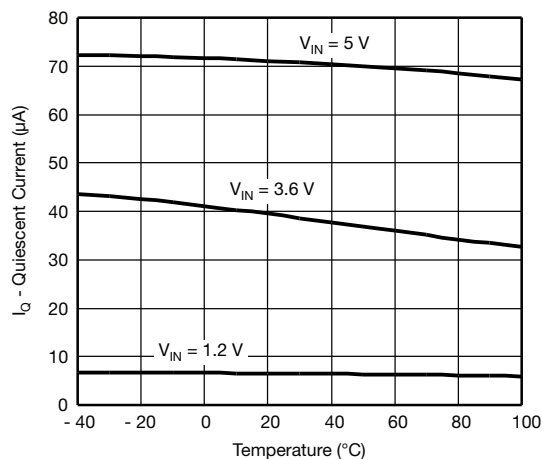


Figure 5 - Quiescent Current vs. Temperature

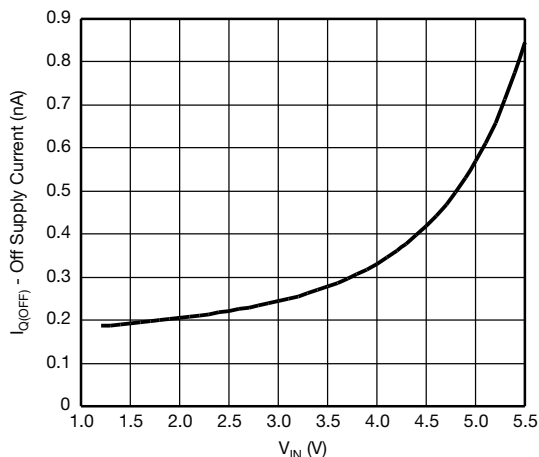


Figure 6 - Off Supply Current vs. Input Voltage

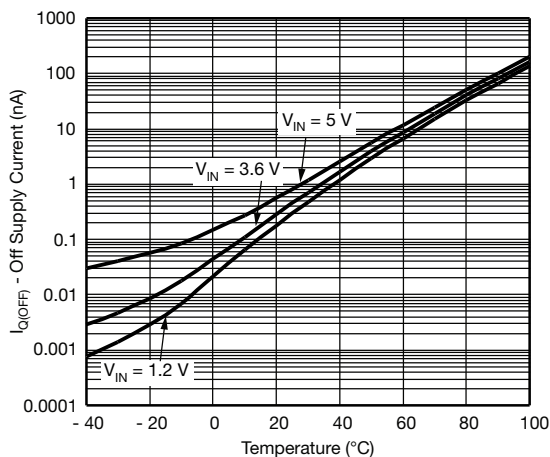


Figure 7 - Off Supply Current vs. Temperature

TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

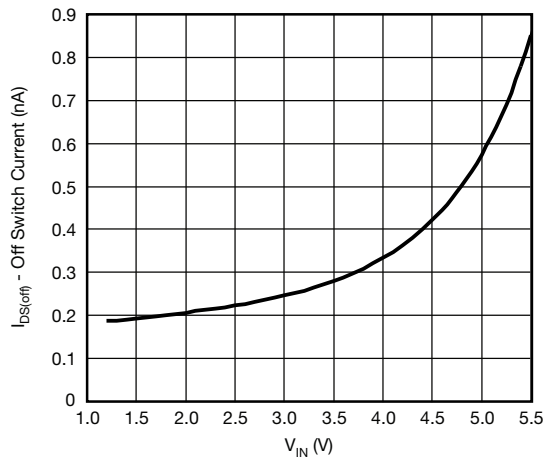


Figure 8 - Off Switch Current vs. Input Voltage

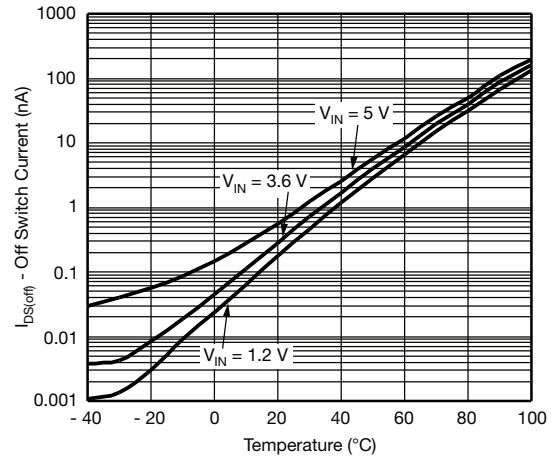


Figure 9 - Off Switch Current vs. Temperature

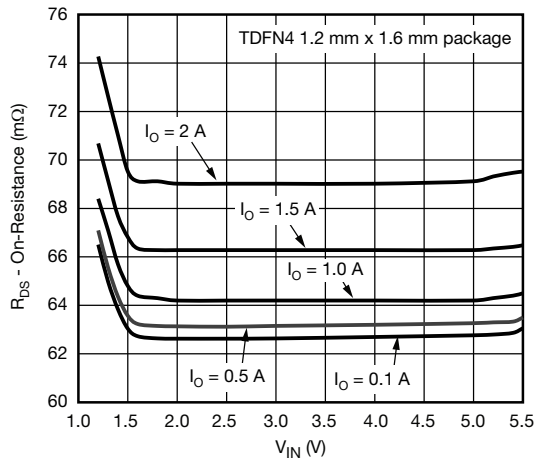


Figure 10 - $R_{DS(on)}$ vs. V_{IN} for TDFN4 package

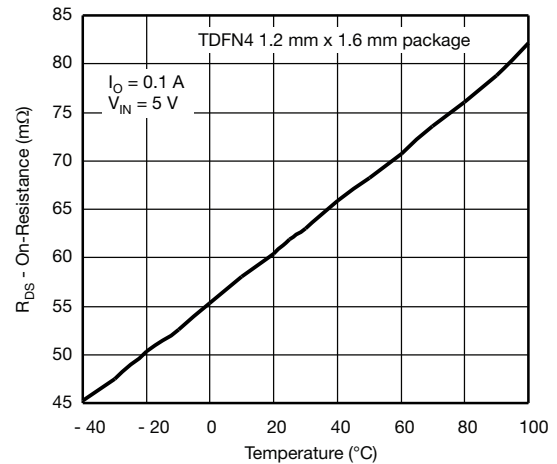


Figure 11 - $R_{DS(on)}$ vs. Temperature for TDFN4 package

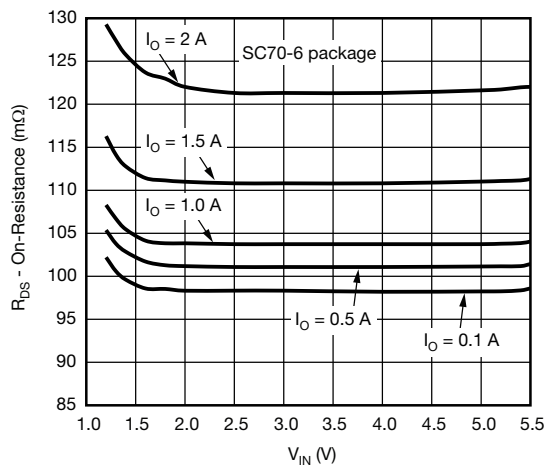


Figure 12 - $R_{DS(on)}$ vs. V_{IN} for SC70-6 package

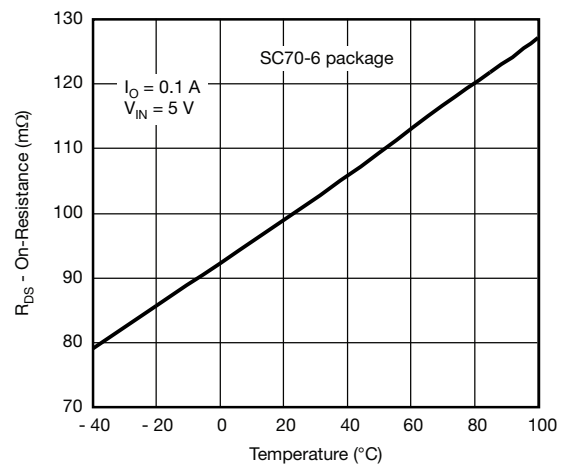


Figure 13 - $R_{DS(on)}$ vs. Temperature for SC70-6 package

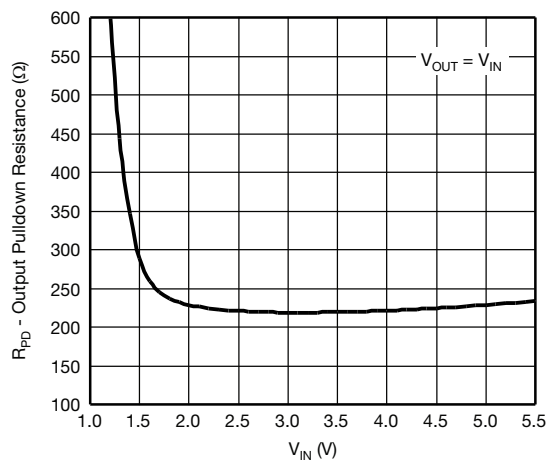
TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

Figure 14 - Output Pull Down vs. Input Voltage

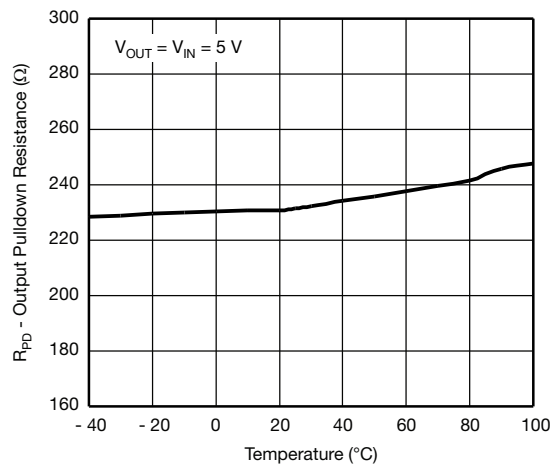


Figure 15 - Output Pull Down vs. Temperature

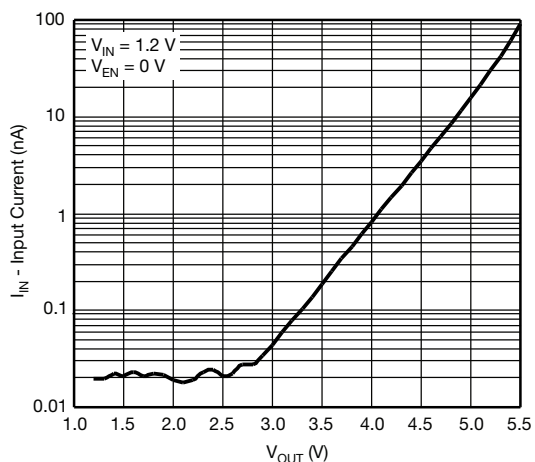


Figure 16 - Reverse Blocking Current vs. Output Voltage

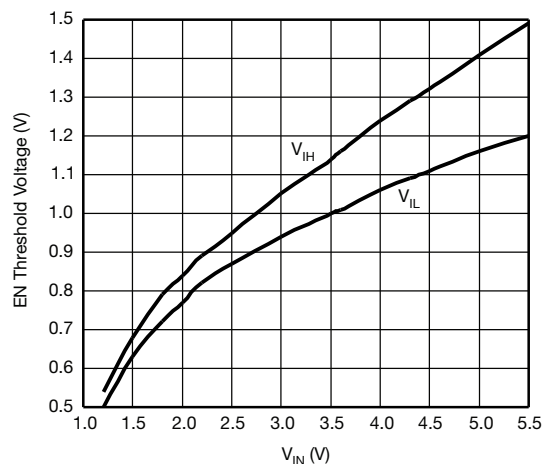


Figure 17 - EN Threshold Voltage vs. Input Voltage

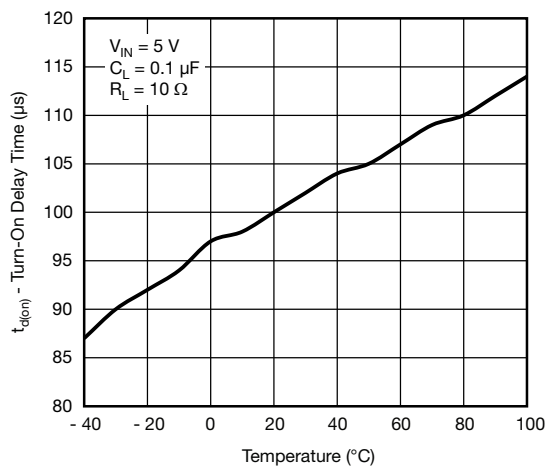


Figure 18 - Turn-On Delay Time vs. Temperature

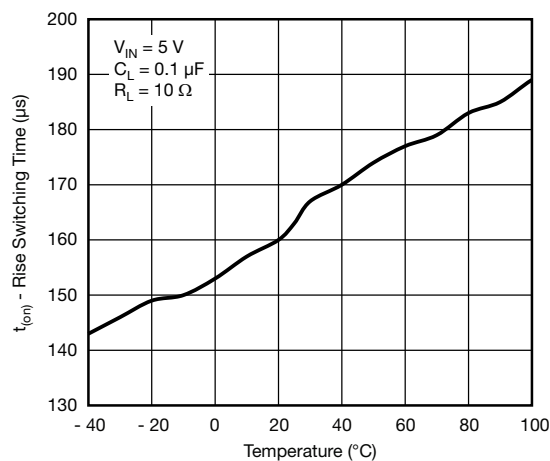


Figure 19 - Rise Time vs. Temperature

TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

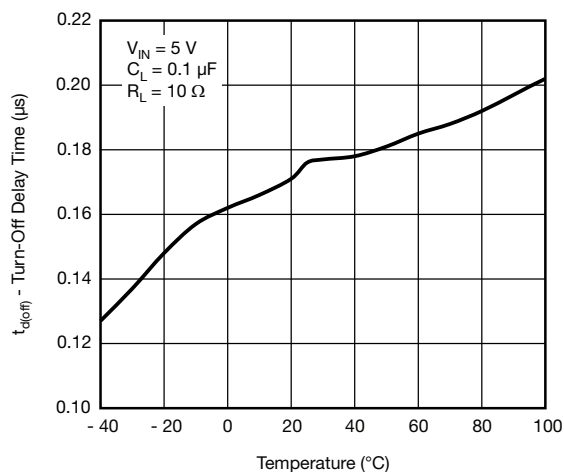


Figure 20 - Turn-Off Delay Time vs. Temperature

TYPICAL WAVEFORMS

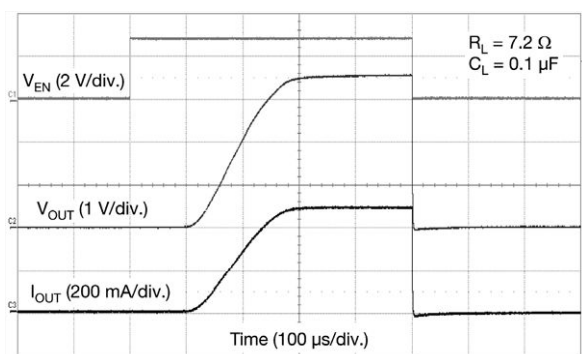


Figure 21 - Switching ($V_{IN} = 3.6\text{ V}$)

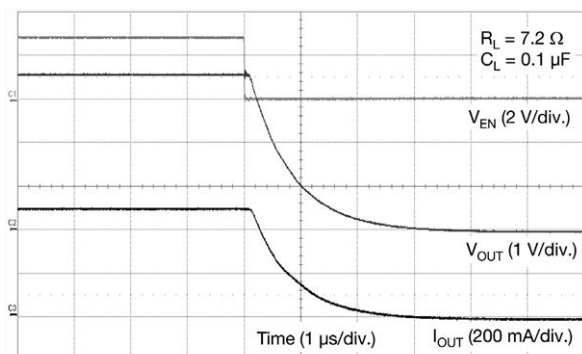


Figure 22 - Turn-Off ($V_{IN} = 3.6\text{ V}$)

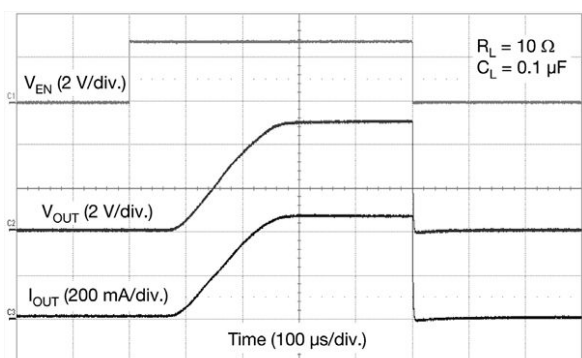


Figure 23 - Switching ($V_{IN} = 5\text{ V}$)

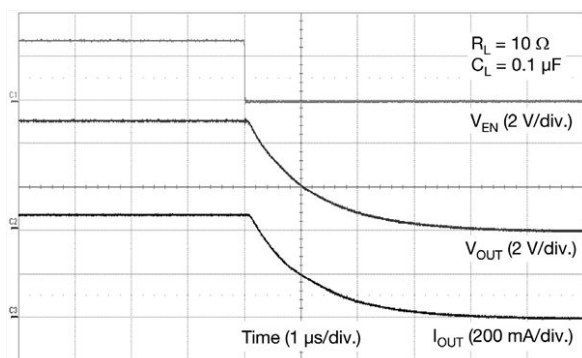


Figure 24 - Turn-Off ($V_{IN} = 5\text{ V}$)

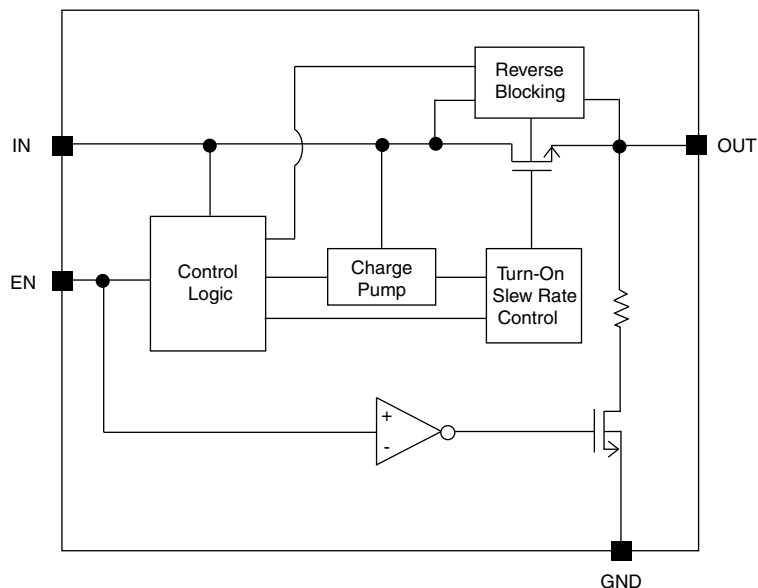
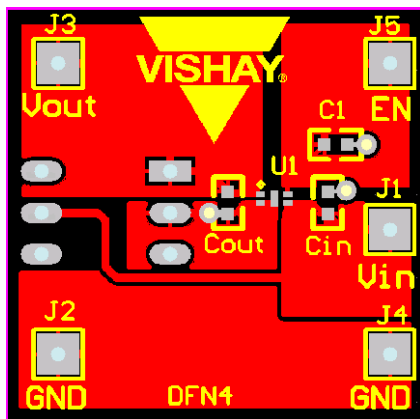
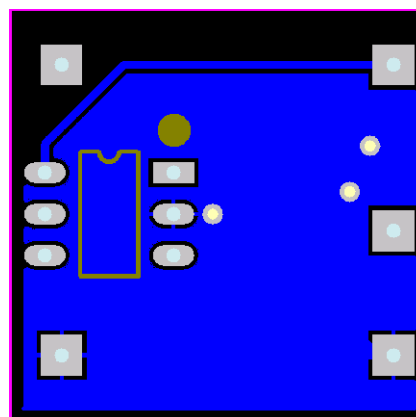
BLOCK DIAGRAM

Figure 25 - Functional Block Diagram

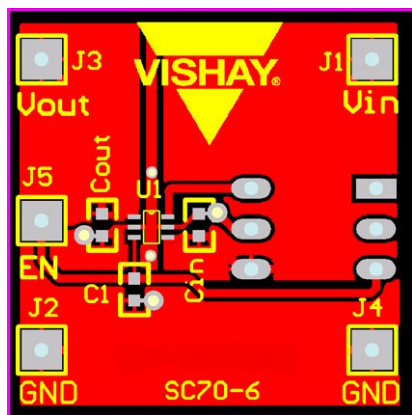
PCB LAYOUT

Top

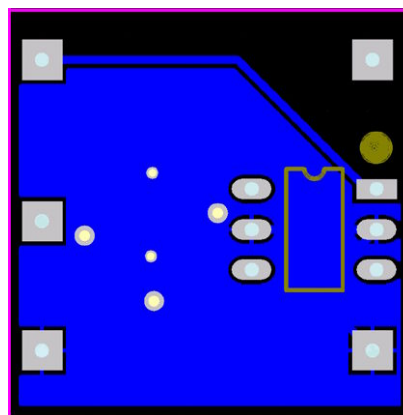


Bottom

Figure 26 - PCB Layout for TDFN4 1.2 mm x 1.6 mm (board size: 1 inch x 1 inch)



Top



Bottom

Figure 27 - PCB Layout for SC70-6 (board size: 1 inch x 1 inch)

**DETAILED DESCRIPTION**

SiP32411 is an n-channel power MOSFET designed as high side load switch with slew rate control to prevent in-rush current. Once enable the device charge pumps the gate of the power MOSFET to 5 V gate to source voltage while controlling the slew rate of the turn on time. The mostly constant gate to source voltage keeps the on resistance low through out the input voltage range. When disable, the output discharge circuit turns on to help pull the output voltage to ground more quickly. Also in disable mode, the reverse blocking circuit is activated to prevent current from going back to the input in case the output voltage is higher than the input voltage. Input voltage is needed for the reverse blocking circuit to work properly, it can be as low as $V_{IN(min)}$.

APPLICATION INFORMATION**Input Capacitor**

While a bypass capacitor on the input is not required, a 2.2 μ F or larger capacitor for C_{IN} is recommended in almost all applications. The bypass capacitor should be placed as physically close as possible to the SiP32411 to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

Output Capacitor

A 0.1 μ F capacitor or larger across V_{OUT} and GND is recommended to insure proper slew operation. C_{OUT} may be increased without limit to accommodate any load transient condition with only minimal affect on the SiP32411 turn on slew rate time. There are no ESR or capacitor type requirement.

Enable

The EN pin is compatible with both TTL and CMOS logic voltage levels.

Protection Against Reverse Voltage Condition

The SiP32411 contains a reverse blocking circuitry to protect the current from going to the input from the output in case where the output voltage is higher than the input voltage when the main switch is off. A supply voltage as low as the minimum required input voltage is necessary for this circuitry to work properly.

Thermal Considerations

The SiP32411 is designed to maintain a constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 1.8 A for SC70-6 package and 2.4 A for TDFN4 package, as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of

240 $^{\circ}$ C/W for SC70-6 and 170 $^{\circ}$ C/W for TDFN4) the power pad of the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependant on the maximum junction temperature, $T_{J(MAX)} = 125^{\circ}\text{C}$, the junction-to-ambient thermal resistance for the TDFN4 1.2 mm x 1.6 mm package, $\theta_{JA} = 170^{\circ}\text{C/W}$, and the ambient temperature, T_A , which may be formulaically expressed as:

$$P(\text{max.}) = \frac{T_J(\text{max.}) - T_A}{\theta_{JA}} = \frac{125 - T_A}{170}$$

It then follows that, assuming an ambient temperature of 70 $^{\circ}$ C, the maximum power dissipation will be limited to about 324 mW.

So long as the load current is below the 2.4 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the $R_{DS(ON)}$ at the ambient temperature.

As an example let us calculate the worst case maximum load current at $T_A = 70^{\circ}\text{C}$. The worst case $R_{DS(ON)}$ at 25 $^{\circ}$ C occurs at an input voltage of 1.2 V and is equal to 75 m Ω . The $R_{DS(ON)}$ at 70 $^{\circ}$ C can be extrapolated from this data using the following formula:

$$R_{DS(ON)}(\text{at } 70^{\circ}\text{C}) = R_{DS(ON)}(\text{at } 25^{\circ}\text{C}) \times (1 + T_C \times \Delta T)$$

Where T_C is 3400 ppm/ $^{\circ}$ C. Continuing with the calculation we have

$$R_{DS(ON)}(\text{at } 70^{\circ}\text{C}) = 75 \text{ m}\Omega \times (1 + 0.0034 \times (70^{\circ}\text{C} - 25^{\circ}\text{C})) = 86.5 \text{ m}\Omega$$

The maximum current limit is then determined by

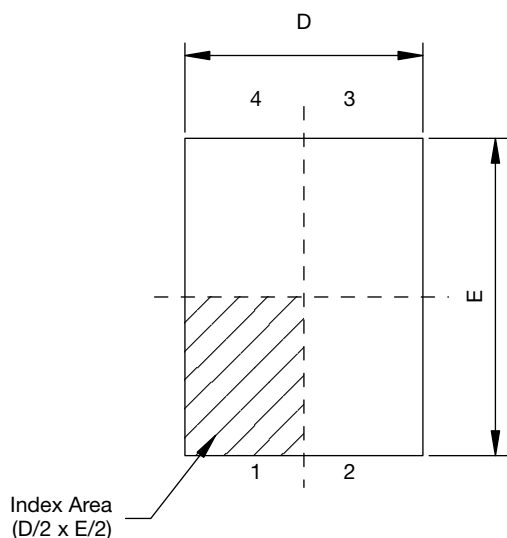
$$I_{LOAD}(\text{max.}) < \sqrt{\frac{P(\text{max.})}{R_{DS(ON)}}}$$

which in case is 1.94 A. Under the stated input voltage condition, if the 1.94 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.

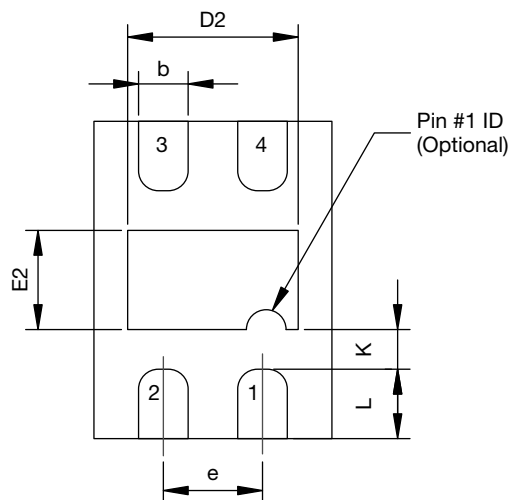
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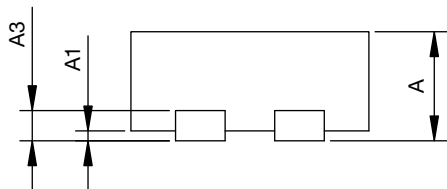
TDFN4 1.2 x 1.6 Case Outline



Top View



Bottom View

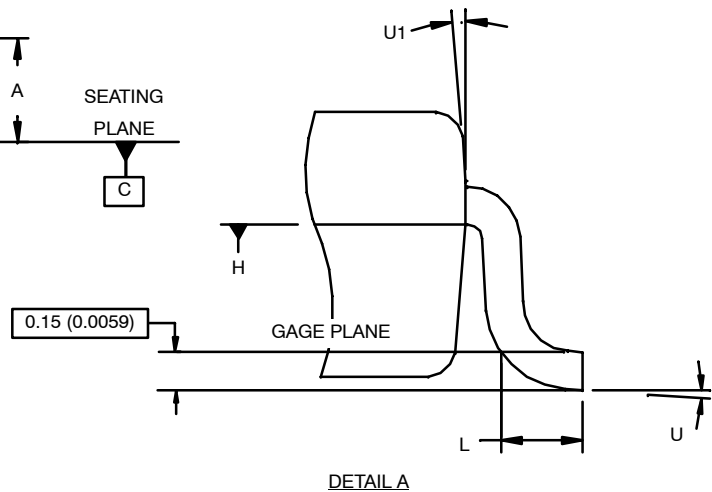
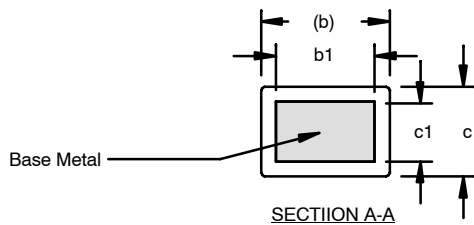
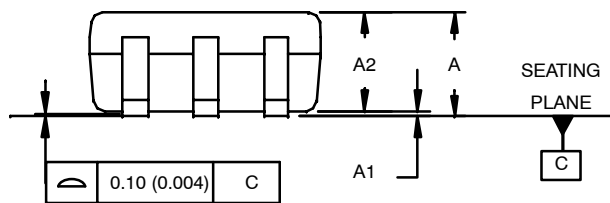
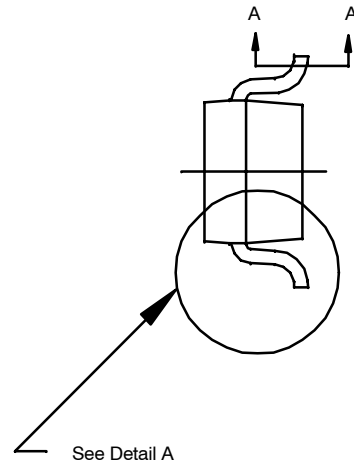
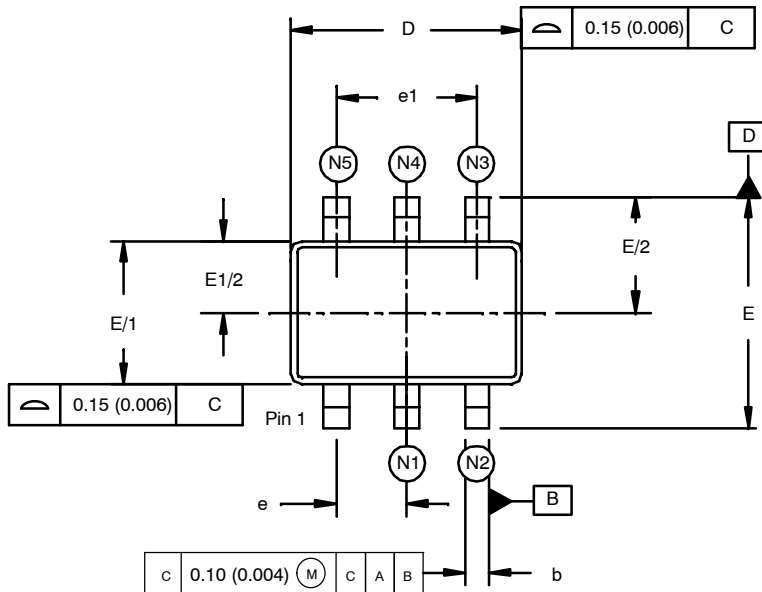


Side View

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	-	0.05	0.00	-	0.002
A3	0.15 REF.			0.006		
b	0.20	0.25	0.30	0.008	0.010	0.012
D	1.15	1.20	1.25	0.045	0.047	0.049
D2	0.81	0.86	0.91	0.032	0.034	0.036
e	0.50 BSC			0.020		
E	1.55	1.60	1.65	0.061	0.063	0.065
E2	0.45	0.50	0.55	0.018	0.020	0.022
K	0.25 TYP.			0.010 TYP.		
L	0.25	0.30	0.35	0.010	0.012	0.014
ECN: S11-2099-Rev. B, 07-Nov-11						
DWG: 5995						



SC-70: 3/4/5/6-LEADS (PIC ONLY)



Pin Code	LEAD COUNT			
	3	4	5	6
N1	–	–	2	2
N2	2	2	3	3
N3	–	3	4	4
N4	3	–	–	5
N5	–	4	5	6

NOTES:

1. Dimensioning and tolerancing per ANSI Y14.5M-1994.
2. Controlling dimensions: millimeters converted to inch dimensions are not necessarily exact.
3. Dimension "D" does not include mold flash, protrusion or gate burr. Mold flash, protrusion or gate burr shall not exceed 0.15 mm (0.006 inch) per side.
4. The package top shall be smaller than the package bottom. Dimension "D" and "E1" are determined at the outer most extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.80	–	1.10	0.031	–	0.043
A1	0.00	–	0.10	0.000	–	0.004
A2	0.80	0.90	1.00	0.031	0.035	0.040
b	0.15	–	0.30	0.006	–	0.012
b1	0.15	0.20	0.25	0.006	0.008	0.010
c	0.08	–	0.25	0.003	–	0.010
c1	0.08	0.13	0.20	0.003	0.005	0.008
D	1.90	2.10	2.15	0.074	0.082	0.084
E	2.00	2.10	2.20	0.078	0.082	0.086
E₁	1.15	1.25	1.35	0.045	0.050	0.055
e	0.65 BSC			0.0255 BSC		
e₁	1.30 BSC			0.0512 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
U	0°	–	8°	0°	–	8°
U1	4°		10°	4°		10°
ECN: S-42145—Rev. A, 22-Nov-04 DWG: 5941						



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